

	Type	L #	Hits	Search Text	DBs
1	BRS	L1	26	nemati near farid.in.	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
2	BRS	L2	33	yang near kevin.in.	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
3	BRS	L3	811	(thyristor) near25 (memory)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
4	BRS	L4	167	(thyristor) near25 (memory near cell)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	Type	L #	Hits	Search Text	DBs
5	BRS	L5	3	((thyristor) near25 (memory near cell)) near15 (electrode)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
6	BRS	L6	22	((thyristor) near25 (memory)) near15 (electrode)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
7	BRS	L7	203	((thyristor) near25 (memory)) and (electrode)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
8	BRS	L8	0	((thyristor) near25 (memory)) and (electrode near15 tempearture)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	Type	L #	Hits	Search Text	DBs
9	BRS	L9	0	((thyristor) near25 (memory)) and (electrode near15 temperature)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
10	BRS	L10	68	((thyristor) near25 (memory)) and (electrode near15 voltage)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
11	BRS	L11	31	10 and (temperature)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
12	BRS	L12	3	((thyristor) near25 (memory)) near25 (electrode near15 voltage)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	Type	L #	Hits	Search Text	DBs
13	BRS	L13	24	((thyristor) near25 (memory)) near25 (electrode)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
14	BRS	L14	131	((thyristor) near25 (electrode)) near25 (temperature)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
15	BRS	L16	1	((((thyristor) near15 (electrode)) near15 (temperature)) same (memory)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
16	BRS	L17	2	((((thyristor) near15 (electrode)) near15 (temperature)) and (memory)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	Type	L #	Hits	Search Text	DBs
17	BRS	L15	102	((thyristor) near15 (electrode)) near15 (temperature)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
18	BRS	L18	0	((thyristor-base near memory) near15 (electrode)) near15 (temperature)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
19	BRS	L19	0	(thyristor-base near memory)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
20	BRS	L20	47	(thyristor-based near memory)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	Type	L #	Hits	Search Text	DBs
21	BRS	L21	1	(thyristor-based near memory) near15 (electrode)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
22	BRS	L22	1	(thyristor-based near memory) same (electrode)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
23	BRS	L23	22	(thyristor-based near memory) and (electrode)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
24	BRS	L24	124	(thyristor near5 memory) and (electrode)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	Type	L #	Hits	Search Text	DBs
25	BRS	L25	0	(thyristor near5 memory) and (electrode near10 temperature)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
26	BRS	L26	34	(thyristor near5 memory) and (electrode near10 voltage)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
27	BRS	L27	8	((thyristor near5 memory) and (electrode)) near15 (anode or cathode)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	U	1	Document ID	Title
1			US 4864168 A	Process for controlling an optical pnpn thyristor to be driven
2			US 4829357 A	PNPN thyristor
3			US 3909805 A	Programmable read only memory
4			US 3885232 A	Apparatus for the treatment of yarn thickness variation signals
5			SU 1281236 A	Sea and fresh water electric fishing gear - has additional electrodes, and positive DC source terminal connected with memory capacitor cover
6			SU 1241298 A	Sequential switching relay e.g. for two fans - has two-input memory switches, resistor and two neutral relays
7	X		SU 1180979 A	Control and computing voltage-switching memory cell - has amorphous switch output connected to anode of thyristor with cathode to null potential rail

	U	1	Document ID	Title
8	X		SU 883545 B	IC engine starter-generator circuit - has memory unit connected to sensor transistor collector with output to indicator to ensure first time start

	U	1	Document ID	Title
1	X		US 6690039 B1	Thyristor-based device that inhibits undesirable conductive channel formation
2	X		US 3758728 A	REPEATER FAULT LOCALIZATION SYSTEM
3	X		SU 1001051 A	Stabilised DC supply - has three diodes and thyristors and output voltage divider with dynistor to reduce switching transient